

T16 16A TRIACs

FEATURES

- Glass Passivated Junctions
- High voltage and surge capability
- Low Thermal Resistance and Durability
- Triggering in three quadrants

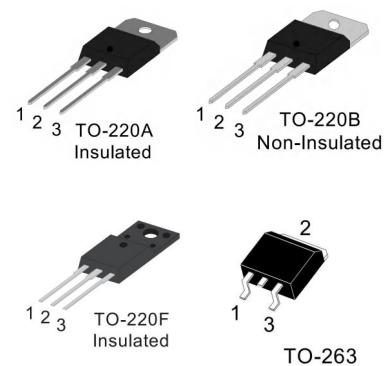
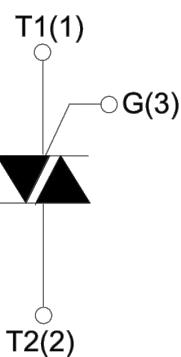
APPLICATIONS

- Static relays
- Heating regulation
- In-duction motor starting circuits
- Phase control operation in light dimmers
- Motor speed controllers



Parameters Summary

VD/VR:600/800/1200V IT(RMS):16A IGT:0.5 to 50mA



ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T _{stg}	-40~150	°C
Operating junction temperature range	T _j	-40~150	°C
Repetitive peak off-state voltage (T = 25°C)	V _{DRM}	600/800/1200	V
Repetitive peak reverse voltage (T = 25°C)	V _{RRM}	600/800/1200	V
RMS on-state current	I _{T(RMS)}	16	A
Non repetitive surge peak on-state current (full cycle, F=50Hz)	I _{TSM}	160	A
I ² t value for fusing (tp=10ms)	I ² t	128	A ² s
Critical rate of rise of on-state current(I = 2×I _{GT})	di/dt	50	A/μs
Peak gate current	I _{GM}	4	A
Peak gate power dissipation	P _{GM}	5	W
Average gate power dissipation	P _{G(AV)}	1	W

Thermal Resistances

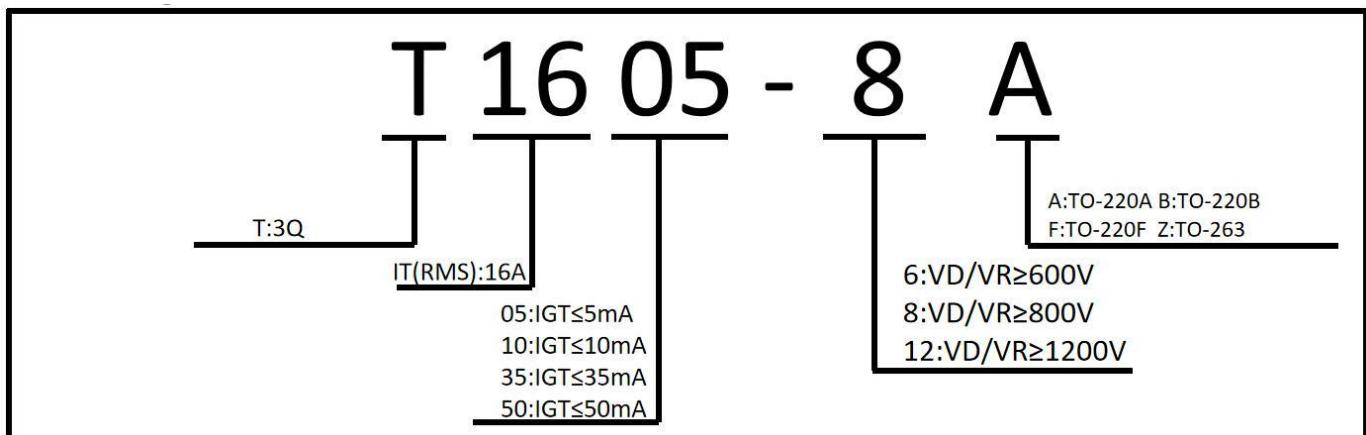
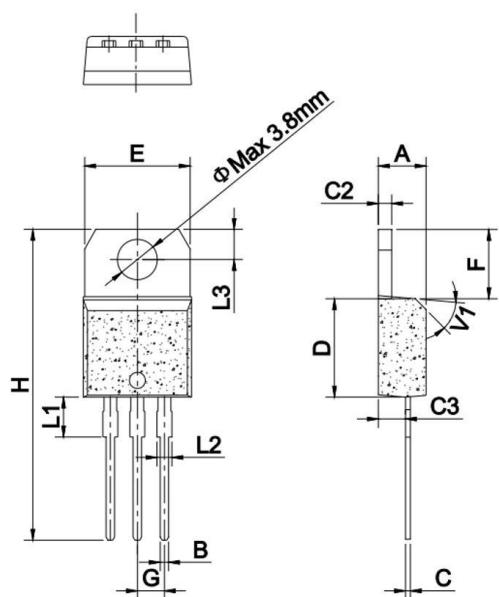
Symbol	Parameter	Value	Unit
R _{th(j-c)}	Junction to case (DC)	TO-220A	2.1
		TO-220B	1.2
		TO-220F	2.3
		TO-263	0.85

ELECTRICAL CHARACTERISTICS (T=25°C unless otherwise specified)

Symbol	Test Condition	Quadrant		Value				Unit
				5	10	35	50	
I _{GT}	V _D =12V, I _T =0.1A, T _j =25°C	I II III	MAX.	5	10	35	50	mA
V _{GT}		I II III	MAX.			1.3		V
V _{GD}	V _D =V _{DRM} T _j =125°C	I II III	MIN.			0.2		V
I _L	I _G =1.2I _{GT}	I-III	MAX.	20	30	50	80	mA
		II		30	40	60	100	
I _H	IT=100mA		MAX.	50	20	40	60	mA
dV/dt	VD=2/3VDRM Gate Open T _j =125°C		MIN.	100	200	500	1000	V/μs

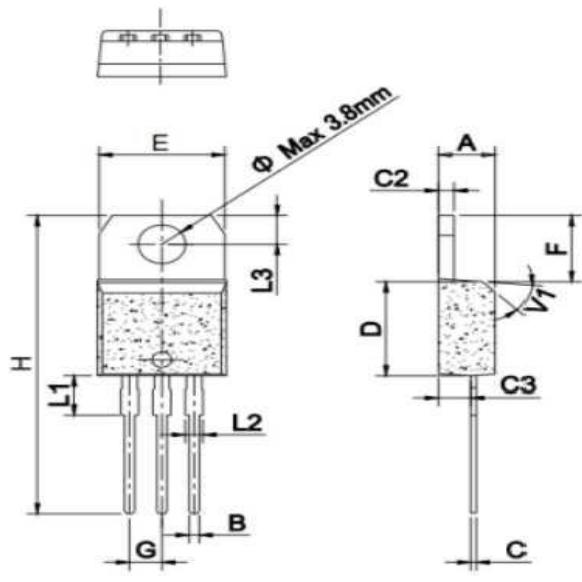
STATIC CHARACTERISTICS

Symbol	Parameter	Value(MAX.)	Unit
V _{TM}	I _{TM} =22.5A tp=380μs	T _j =25°C	V
I _{DRM}	V _D =V _{DRM} V _R =V _{RRM}	T _j =25°C	μA
I _{RRM}		T _j =125°C	mA

Ordering Information Scheme

TO-220A Package Mechanical Data


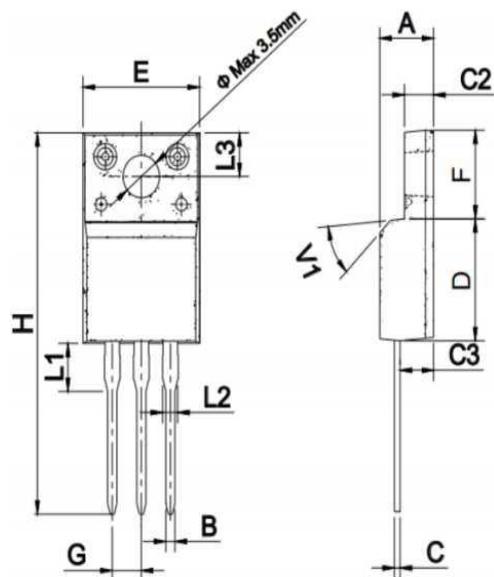
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.80		10.4	0.386		0.409
F	6.55		6.95	0.258		0.274
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	

TO-220B Package Mechanical Data



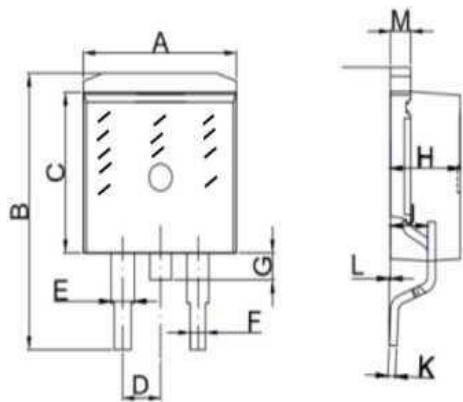
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.10		4.30	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
D	1.21		1.32	0.048		0.052
E	2.40		2.72	0.094		0.107
F	8.60		9.70	0.339		0.382
G	9.60		10.4	0.378		0.409
H	6.25		7.05	0.244		0.260
J		2.54			0.1	
K	28.0		29.8	1.102		1.173
N					0.148	
P	1.14		1.70	0.045		0.067
V	2.65		2.95	0.104		0.116

TO-220F Package Mechanical Data



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.50		4.90	0.177		0.193
B	0.74	0.80	0.83	0.029	0.031	0.033
C	0.47		0.65	0.019		0.026
C2	2.50		3.10	0.096		0.108
C3	2.40		2.80	0.102		0.118
D	8.60		8.90	0.346		0.366
E	9.80		10.4	0.386		0.410
F	6.70		7.50	0.252		0.268
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.63			0.143	
L2	1.14		1.70	0.045		0.067
L3		3.30			0.130	
V1		45°			45°	

TO-263 Package Mechanical Data



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.90		10.5	0.390		0.402
B	14.70		15.80	0.579		0.622
C	8.8		9.2	0.37		0.378
D		2.54			0.100	
E	1.20		1.40	0.047		0.055
F	0.75		0.85	0.029		0.033
G			1.75			0.069
H	4.40		4.70	0.173		0.185
J	2.30		2.70	0.091		0.106
K	0.38		0.55	0.015		0.022
L	0		0.25	0	0.004	0.010
M	1.25		1.35	0.049		0.053

FIG.1 Maximum power dissipation versus on-state current

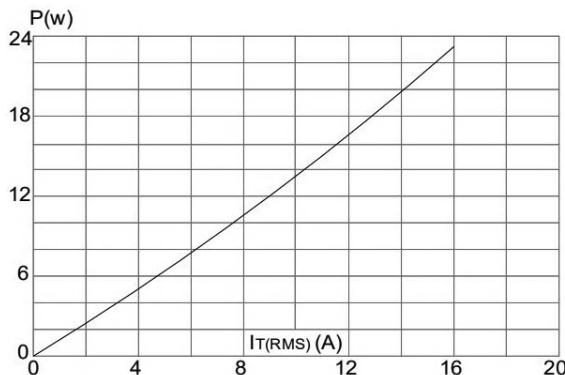


FIG.3: Surge peak on-state current versus number of cycles

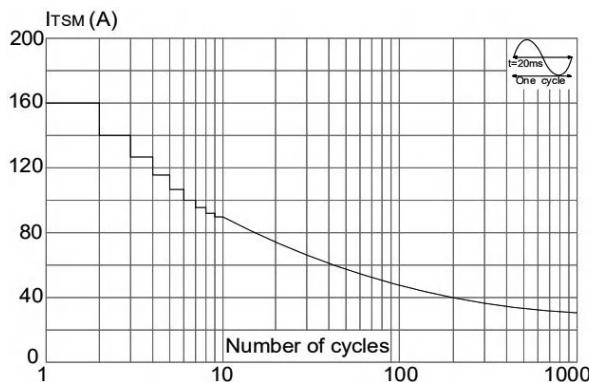


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$, and corresponding value of $I_2 t$ ($dI/dt < 50\text{A}/\mu\text{s}$)

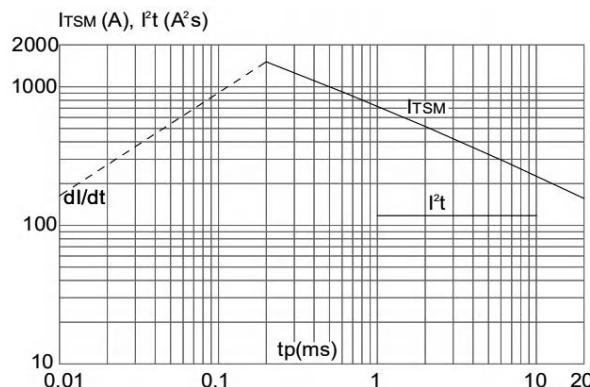


FIG.2: on-state current versus case temperature

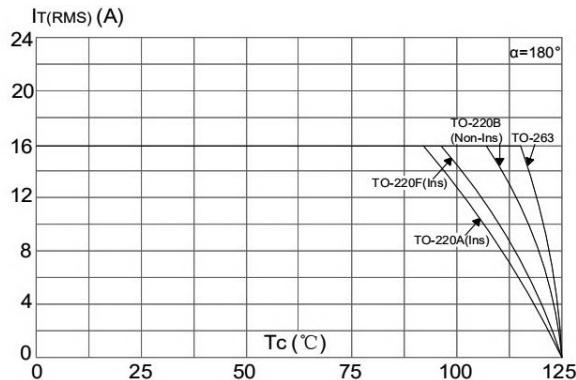


FIG.4: On-state characteristics (maximum values)

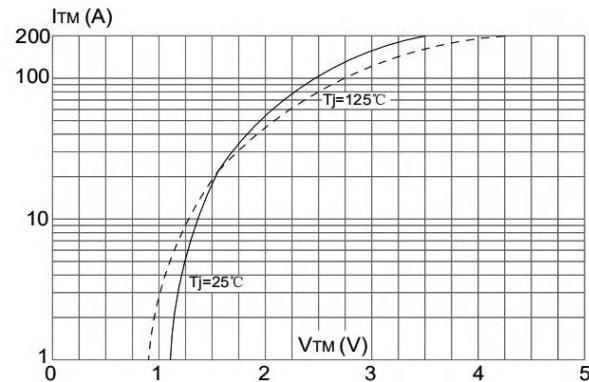
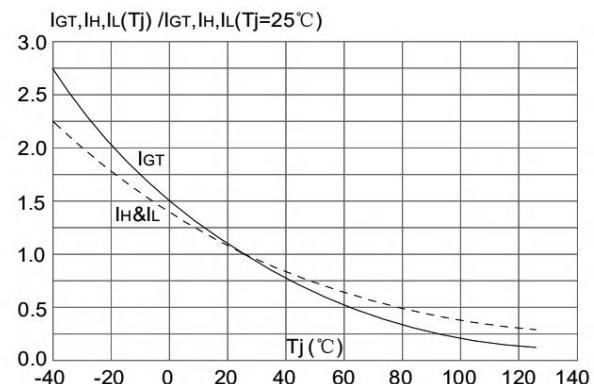


FIG.6: Relative variations of gate trigger current holding current and latching current versus junction temperature



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